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Qi, Xiaozhuo; Lo, Tsz Wing; Liu, Di; Feng, Lantian; Chen, Yang; Wu, Yunkun; Ren, Hongliang; Guo, Guang-Can; Lei, Dangyuan; Ren, Xifeng

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Effects of gap thickness and emitter location on the photoluminescence enhancement of monolayer MoS\(_2\) in a plasmonic nanoparticle-film coupled system

Abstract: Plasmonic nanocavities comprised of metal film-coupled nanoparticles have emerged as a versatile nanophotonic platform benefiting from their ultrasmall mode volume and large Purcell factors. In the weak-coupling regime, the particle-film gap thickness affects the photoluminescence (PL) of quantum emitters sandwiched therein. Here, we investigated the Purcell effect-enhanced PL of monolayer MoS\(_2\) inserted in the gap of a gold nanoparticle (AuNP)–alumina (Al\(_2\)O\(_3\))–gold film (Au Film) structure. Under confocal illumination by a 532 nm CW laser, we observed a 7-fold PL peak intensity enhancement for the cavity-sandwiched MoS\(_2\) at an optimal Al\(_2\)O\(_3\) thickness of 5 nm, corresponding to a local PL enhancement of ∼350 by normalizing the actual illumination area to the cavity’s effective near-field enhancement area. Full-wave simulations reveal a counterintuitive fact that radiation enhancement comes from the non-central area of the cavity rather than the cavity center. By scanning an electric dipole across the nanocavity, we obtained an average radiation enhancement factor of about 65 for an Al\(_2\)O\(_3\) spacer thickness of 4 nm, agreeing well with the experimental thickness and indicating further PL enhancement optimization. Our results indicate the importance of configuration optimization, emitter location and excitation condition when using such plasmonic nanocavities to modulate the radiation properties of quantum emitters.

Keywords: nanoparticle-film coupled system; photoluminescence enhancement; plasmonic nanocavity; transition-metal dichalcogenides.

1 Introduction

Transition-metal dichalcogenides (TMDs) \([1]\), as an exceptional class of two-dimensional (2D) post-graphene materials, have attracted a great deal of attention from both fundamental research and technological applications. Their bandgaps range from 1 to 2 eV \([2–4]\) and change from indirect to direct when the bulk/multi-layer TMDs are exfoliated to monolayers \([5]\). TMDs-based applications in optics and optoelectronics, such as quantum light sources \([6]\), field-effect transistors \([7]\), photodetectors \([8, 9]\), and flexible optoelectronic diodes \([10]\), have been widely reported. Among various TMDs materials, monolayer molybdenum disulfide (MoS\(_2\)) has a direct bandgap of 1.8 eV \([11]\), which gives rises to photoluminescence (PL) at visible wavelengths and is favorable for optical devices. However, the PL quantum efficiency of
bare monolayer MoS$_2$ is only about 1% owing to its thickness-limited weak light absorption [12]. Therefore, various photonic approaches such as surface plasmon polaritons (SPPs), which have been widely utilized in nanophotonics [13–15], data storage [13], solar cells [16], metasurface [17], and bio-sensing [18], owing to their great field enhancement and field confinement beyond the optical diffraction limit, have been proposed to enhance the PL emission of monolayer MoS$_2$.

One of the most common plasmonic configurations used for the PL enhancement of TMDs is metallic nanoparticles, which behave like optical nanoantennas [19–21]. However, the nanoparticle-film coupled plasmonic configuration, e. g., gold nanoparticles on a gold film with a dielectric spacer in between, exhibits a more strongly localized electric field in the gap between the nanoparticle and film [22, 23]. This has been demonstrated in several applications such as chemical reaction detection [24], strong coupling [25, 26], and surface-enhanced Raman scattering of molecules [27–29]. An isotropic metal nanosphere placed on a metal surface, which shows new features such as sensitivity to the polarization of incident light [30], is the simplest nanoparticle-film coupled configuration. In contrast to a number of experimental studies on the different shapes of nanoparticles [31, 32], studies on the thickness of the gap are scarce. However, the thickness of the gap plays an important role in the nanoparticle-film coupled plasmonic configuration, since it affects the density and modes of local confined fields [33, 34]. In recent studies, the gap thickness has been altered by changing the thickness of the spacer, which combines the emitters coupled with the plasmonic configuration. This method makes it impossible to study the coupling effect or the PL enhancement effect with the confined field at a certain position within the gap. A detailed study on the effect of gap thickness in PL enhancement in the nanoparticle-film coupled plasmonic configuration can be performed if a TMDs monolayer is inserted into the gap, which is filled by a dielectric material. Previous studies on SPPs have shown that the plasmonic resonance provides a stronger electric field as the emitter approaches the metallic surface. When the emitter is too close to the metallic surface (below 10 nm), decay via non-radiative channels dominates, which is known as fluorescence quenching [35, 36]. These effects compete in nanoparticle-film coupled plasmonic configurations, depending on the thickness of the dielectric spacer. Thus, a comprehensive study of the effect of the dielectric spacer thickness is required to provide insight into the PL enhancement process using a nanoparticle-film coupled plasmonic configuration.

In this study, we investigated the PL enhancement of monolayer MoS$_2$ using a gold nanoparticle (AuNP)–aluminum oxide (Al$_2$O$_3$)–gold film (AuFilm) coupled nanocavity system, which refers to a configuration with gold nanoparticles on top of a gold film spaced by Al$_2$O$_3$. Here, the Al$_2$O$_3$ spacer consists of two Al$_2$O$_3$ layers with the same thickness (t), in which the monolayer MoS$_2$ is sandwiched. We measured the PL spectral profile and intensity of monolayer MoS$_2$ in the coupled system for Al$_2$O$_3$ spacer thicknesses of t = 0, 3, 5, and 7 nm and determined an optimal Al$_2$O$_3$ layer thickness for obtaining maximum PL intensity enhancement of MoS$_2$. We performed full-wave electromagnetic simulations to interpret the experimental results through modeling the excitonic emission of MoS$_2$ as the radiation by an electric dipole located in the same nanocavity, and found that the dipole radiation enhancement comes from the cavity’s non-central area because at the cavity center a non-radiative quadrupole plasmon mode is induced at the excitation wavelength. Our study points out that the gap thickness and emitter location influence the Purcell effect of quantum emitters coupled to a plasmonic particle-on-film nanocavity, and is important to the field of plasmon-based fluorescence and Raman spectroscopies.

2 Materials and methods

2.1 Sample preparation

2.1.1 Chemical vapor deposition (CVD) of monolayer: MoS$_2$ on SiO$_2$/Si substrate. Monolayer MoS$_2$ was grown on a SiO$_2$/Si substrate in a quartz tube furnace at atmospheric pressure by a chemical vapor deposition (CVD) method. The thickness of SiO$_2$ was 300 nm. Prior to growth, SiO$_2$/Si substrates were cleaned by sonication in acetone, absolute ethanol, and distilled water for 20 min. The substrates were then placed face-down above the ceramic boat filled with 30 mg of MoO$_3$, which was placed at the center of the quartz tube. Another ceramic boat filled with sulfur (10 mg) was located upstream of the tube at a distance of 12 cm from the center. After purging the system with ultrahigh-purity argon for 20 min, the furnace was kept at 650 °C for 5 min at a heating rate of 15 °C/min.

2.1.2 Al$_2$O$_3$ film deposition and film thickness determination: Alumina film deposition (ALD) is a mild and highly precise technique for the deposition of thin films. All our Al$_2$O$_3$ films were deposited by alternating the exposure of H$_2$O and trimethylaluminum (TMA, Al(CH$_3$)$_3$) at 120 °C. The deposition cycle consisted of: (1) 10 ms H$_2$O pulses, (2) 10 s purge time (17 sccm N$_2$), (3) 15 ms pulses of TMA, and (4) 15 s purge time (17 sccm N$_2$). The Al$_2$O$_3$ film thickness is linear with the number of reaction cycles when the growth conditions remain unchanged. We were able to determine the thickness of the gradually deposited Al$_2$O$_3$ film at each step by calibrating the total deposition reaction cycles to the final film thickness. The standard deviation of
surface roughness for the Al₂O₃ layer on top of MoS₂ is about 1.4 nm (1.0 nm from the Au film and 0.4 nm from the Al₂O₃ film).

2.1.3 KOH-based wet transfer: MoS₂ monolayers were transferred from the SiO₂/Si substrate using the wet transfer KOH method. Samples were first spin-coated with PMMA at 2,000 rpm, and then detached in a KOH solution (30%), washed several times in DI water, and transferred onto either bare or Al₂O₃-coated Au films. These samples were then heated up to 180°C to obtain dry samples. We used acetone to clean the PMMA and blow-dry the sample by clean N₂ from IPA solution.

2.2 Optical characterization: Raman spectroscopy and scanning confocal micro-spectroscopy

To determine the layer number of MoS₂ flakes used in this work, we measured the Raman spectrum of a MoS₂ flake on Si substrate using a confocal Raman spectrometer. Figure S1 displays the Raman spectra of the monolayer MoS₂ that we used. In the Raman spectra, two modes E₁₃₅ (in-plane) and A₄₅ (out-of-plane) separated by ~20 cm⁻¹ are clearly observed, which is typical for monolayer MoS₂ [37]. To measure the PL spectra of nanocavity-sandwiched monolayer MoS₂ and control sample, we used the experimental setup of the scanning confocal micro-spectroscopy system shown in Figure S2. In this system, a continuous-wave laser at 532 nm is transmitted through a polarizer to produce a spectroscopy system shown in Figure S2. In this system, a continuous-wave laser at 532 nm is transmitted through a polarizer to produce a linear-polarized beam, which then excites the sample deposited on a three-axis piezo stage through an objective (OLYMPUS, N.A. = 0.9, 100×). The emission from the sample was collected with the same objective and detected with a single photon avalanche diode (SPAD). A dichroic plate was used to block the 532 nm laser and transmit the PL light (from a white light source) transmitted through the objective. The emission from the sample was collected with the same objective and detected with a single photon avalanche diode (SPAD). The emission from the sample was collected with the same objective and detected with a single photon avalanche diode (SPAD). The emission from the sample was collected with the same objective and detected with a single photon avalanche diode (SPAD).

2.3 Numerical simulations

We performed numerical simulations on the AuNP–Al₂O₃–AuFilm coupled system using Numerical FDTD to obtain a better interpretation of our experimental results obtained earlier [38]. We used two-step calculation to simulate the total emission enhancement of the AuNP–Al₂O₃–AuFilm. The dielectric constant of gold was obtained from Johnson and Christy date [39], and the refractive index of SiO₂ layer was set as 1.5. A total-field scattered-field source at 532 nm was used to excite the 200 nm AuNP on 150 nm AuFilm at normal incidence. In simulation, two orthogonal electric dipoles were set in the gap separately to mimic zero-valley-polarization emissions of monolayer MoS₂ at room temperature. These dipoles were displaced from the center of the particle-field gap to mimic the emissions from multiple dipoles in the monolayer MoS₂. Mesh discretization was set to be 0.5 nm inside the dielectric spacer region and gradually increased outside the sandwiched dielectric region. The total power emitted by the dipole was obtained by integration the Poynting vector of a 3 nm power box surrounding the dipole while the total power radiated outside the nanostructure was obtained by integration the Poynting vector of a 1,000 nm power box surrounding the nanostructure.

3 Result and discussion

As described earlier, we used the CVD method to prepare the monolayer MoS₂ used in the experiment [40–43]. We obtained the reference sample as shown in Figure 1A, by transferring it onto the SiO₂ substrate whose thickness is 300 nm. The sample for the AuNP–AuFilm coupled system is shown in Figure 1D, where a gold film of thickness of 150 nm is deposited between the monolayer MoS₂ and SiO₂ substrate. The AuNP on top of monolayer MoS₂ has a diameter of 200 nm. More details about the sample preparation procedures can be found in the Supplementary Material.

The samples were characterized using the experimental setup described previously. The results are shown in Figure 1. Figure 1B and C are for bare MoS₂ while Figure 1E and F are for the sample with the AuFilm. According to the PL maps in Figure 1B and E, a pronounced PL enhancement of up to six was observed at the position where the AuNP and AuFilm were coupled. We selected the positions with and without AuNPs as indicated by the red arrow and dashed circles in Figure 1B and E, and recorded the corresponding PL spectra, as shown in Figure 1C and F. In Figure 1C, the spectra (black curve) have two peaks located at 680 and 623 nm, which correspond to the A₁ and B₁ band transitions, respectively, of MoS₂, and are consistent with the measurements for bare MoS₂ in the literature [44]. In Figure 1F, we observe that the PL spectra with AuNPs (red curve) exhibit a significant enhancement at the A₁ band, compared to that without AuNPs (blue curve). For simplicity, we used the peaks at the A₁ band to characterize the PL enhancement of our samples. We denote the counts at the A₁ band as N_coupled and N_film for the red and blue curves, respectively. Taking into account the dark count N_dark of the spectrometer, the PL enhancement factor is defined as (N_coupled−N_dark) / (N_film−N_dark). In our case, the value N_dark = 600 is obtained by measuring the samples without any excitation laser. It is to be noted that we used the spectra obtained from the same MoS₂ sample (red and blue curves) for a fair comparison, rather than the red and black curves from different MoS₂ samples. In addition to the pronounced peak intensity enhancement, we also observe a clear blue-shift in the PL peak for the nanocavity-sandwiched MoS₂ in comparison to the same MoS₂ flake on the Au film. This may be due to gap plasmon induced dark exciton emission from the sandwiched MoS₂ [45–49].

Using the above definition, we obtained the PL enhancement factor of AuNP–Al₂O₃–AuFilm coupled system for the sample shown in Figure 1D. We now demonstrate the tuning of this PL enhancement factor by introducing dielectric spacers between the MoS₂ and the gold nanostructures. As illustrated in Figure 2A, two layers...
of Al₂O₃ with a thickness of t were deposited before and after the monolayer MoS₂ was transferred onto the AuFilm. These formed spacers between MoS₂ and the plasmonic components (i.e., AuFilm and AuNP), modifying the gap between AuFilm and AuNP, and hence, the electric field exciting MoS₂. In Figure 2B–D, the experimentally measured PL for three different samples are displayed, where the thicknesses of the Al₂O₃ spacer are t = 3 nm (Figure 2B), t = 5 nm (Figure 2C), and t = 7 nm (Figure 2D), respectively. The bright spots, which can be found in either the PL maps or the SEM images (as insets), indicate the presence of AuNPs. As before, we selected the areas with (red arrows) and without (black circles) AuNPs, and collected the PL spectra as shown in Figure 2E–G, respectively. Similar to the case where t = 0 (Figure 1F), the PL spectra show overall enhancement when AuNPs are involved. The peak at the A₁ band exhibited the best enhancement when t = 5 nm. For t = 3 nm, the field enhancements are comparable for both the A₁ and B₁ bands, such that the peak at the A₁ band is indistinct. As the spacer thickness further increases, the gap between AuNP and AuFilm increases as well, resulting in a weaker electric field that excites the MoS₂. Figure S3 shows experimentally-measured results of other samples.

According to the definition of the PL enhancement factor in section 2, we extracted the PL enhancement factors at the A₁ band for different spacer thicknesses, as shown in Figure 3. Using the same thickness for four samples, the average PL enhancement factors determined are 4.38 for t = 0 nm, 6.89 for t = 3 nm, 7.74 for t = 5 nm and 2.22 for t = 7 nm, respectively. Thus, the enhancement effect of the AuNP–Al₂O₃–AuFilm coupled system is optimal when the thickness of the Al₂O₃ spacer is 5 nm. We reorganized the enhancement factors of the intensity of the PL maps and the enhancement factors of the spectra peaks in Figure S4. The average PL emission counts of the t = 3 nm samples was higher than other samples, because of the broad spectra enhancement.

Figure 4A displays the schematic diagram of the AuNP–Al₂O₃–AuFilm with the Al₂O₃ spacer thickness varying from 2 to 12 nm. For simplicity, monolayer MoS₂ is regarded as a dielectric layer with a thickness of 1 nm in the simulations [11]. Thus, the total spacer thickness varies from 3 to 13 nm. An in-plane dipole with parallel or perpendicular polarization from the displace axis is used to represent the excitonic emission of the MoS₂ monolayer. In our experiment, the 532 nm pump light was focused on the sample after passing through the objective lens. Since the
excitonic response in monolayer MoS$_2$ is more sensitive to the in-plane electric component, we focus on the electric field component $E_x$ and also approximate the 532 nm Gaussian excitation as a simple plane wave at normal incidence. In the 532 nm excitation, the charge distribution is dominated by the transverse mode in the AuNP–AuFilm system, as shown in Figure 4B. The charge distribution confined in the gap is highly similar to an electric quadrupole, which forms two hot spots in the TMDC monolayer. The two hot spots, which are dominated by out-of-plane field component, show antiphase oscillation (Figure 4C). When the gap broadens, the localized electric field enhancement is weakened (Figure 4D) due to the reduced coupling with the image charge in the gold film substrate.

We first consider both the orthogonal in-plane dipoles to contribute equally to the enhancement of excitonic emission in the Au-NP film as the degree of valley polarization is insignificant at room temperature. In addition, the enhancement of excitonic emissions along the spectra is simplified by considering the enhancement of emission at 650 nm only because this wavelength lies between the A and B exciton emissions. The quantum efficiency of MoS$_2$ is assumed to be approximately 1% [12].

![Figure 2](image1)

**Figure 2:** (A) Schematic representation of AuNP–AuFilm coupled system with Al$_2$O$_3$ spacers. (B–D) PL intensity maps of monolayer MoS$_2$ samples. Insets: SEM image of each sample type. The thickness of the spacer is (B) 3 nm (C) 5 nm (D) 7 nm. (E–G) PL spectra of monolayer MoS$_2$ with and without AuNPs (red and blue curves), corresponding to the position in (B–D) (red arrow and black dashed circle, respectively).

![Figure 3](image2)

**Figure 3:** PL enhancement factors for the spectra at the A1 bands using different spacer thicknesses. The thickness of the Al$_2$O$_3$ spacer was 0, 3, 5, and 7 nm.

![Figure 4](image3)

**Figure 4:** (A) Schematic representation of Al$_2$O$_3$ spacers. (B) PL intensity maps of monolayer MoS$_2$ samples. Insets: SEM image of each sample type. The thickness of the spacer is (B) 3 nm (C) 5 nm (D) 7 nm. (E–G) PL spectra of monolayer MoS$_2$ with and without AuNPs (red and blue curves), corresponding to the position in (B–D) (red arrow and black dashed circle, respectively).
transition of the gap thickness. To understand the detailed mode distribution at the excitation wavelength, the in-plane view of mode distribution is also shown in Figure S5, which reveals that both the electric field x-component (Figure S5a) and the y-component (Figure S5c) for the 3 nm spacer thickness demonstrate more complex distribution patterns than that for the 13 nm spacer thickness (Figure S5b and d) due to the stronger mode hybridization in the former system. As a result, the average enhancement along the displace axis is maximized when the spacer is approximately 8 nm wide (Figure 4F), which is consistent with the experimentally observed result. Although the above simulation focuses only on the line distribution of emission enhancement rather than the total enhancement, it provides a good agreement with the experimental result. It was calculated that the effective radius of near-field enhancement is 30 nm and the area of effective near-field enhancement is $\sim 2.8 \times 10^{-3} \mu m^2$ from the simulation results [50]. Theoretically, the focused laser spot radius is about 200 nm and the actual illumination area is $\sim 0.126 \mu m^2$. Because the actual illumination area is much larger than the effective plasmonic near-field enhancement area, the plasmon-induced PL intensity enhancement factor should be adjusted accordingly [22]. In our work, the adjusted PL enhancement factor is about 350 for $t = 5 \text{ nm}$.

A comprehensive comparison of the experiment and numerical simulations showed that coupling hybridized modes did not enhance PL spectra as the charge distribution in the quadrupole mode. When $t = 3 \text{ nm}$ in the experiment, the enhancement is not as remarkable as the deformation of the spectra (see Figure 2E). Therefore, even though the 3 nm thickness spacer provides a stronger localized electric field enhancement, the actual enhancement effect is not ideal in the AuNP–Al$_2$O$_3$–AuFilm coupled system. The electric field confined results from the hybridized mode, which is influenced by the charge distribution mode. This is possibly related to the in-plane polarization properties of TMD materials. In a weak coupling system, choosing an appropriate confined electric field mode is more beneficial for the efficient enhancement of the desired spectra profile. We also consider possible factors leading to the slight deviation between the simulated and experimental optimal spacer thicknesses. The AuNP–Al$_2$O$_3$–AuFilm coupled system in the numerical simulation is idealized as a perfect Au nanosphere sitting on a perfectly flat Au film separated by two smooth Al$_2$O$_3$ layers. This assumption deviates from the actual experimental conditions. The colloidal Au nanoparticle used in the experiment could have small facets supporting more complex resonance modes such as cavity
modes that hybridize with both the transverse and gap plasmon modes [31, 51]. Meanwhile, the surface roughness of Au and Al2O3 films might induce irregular features in the particle-film gap and local strain in MoS2 [52], which both can affect the PL enhancement and the intrinsic quantum efficiency of MoS2.

4 Conclusion

We studied the PL spectral enhancement of monolayer MoS2 sandwiched in an AuNP–Al2O3–AuFilm coupled nanocavity by systematically changing the Al2O3 spacer thickness (i.e., the cavity gap thickness). Our experiment shows that a thickness of approximately 4 nm, which could be due to the influence of the charge distribution mode. These results could be widely used in Purcell enhancement experiments with such plasmonic particle-on-film nanocavities to enhance the emission properties of quantum emitters. Our plasmonic nanocavities can also be used to control the emission properties of more general 2D materials [53] and other dual-resonant optical materials [54, 55].

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